2SK1266

Silicon N-channel Power F-MOS FET

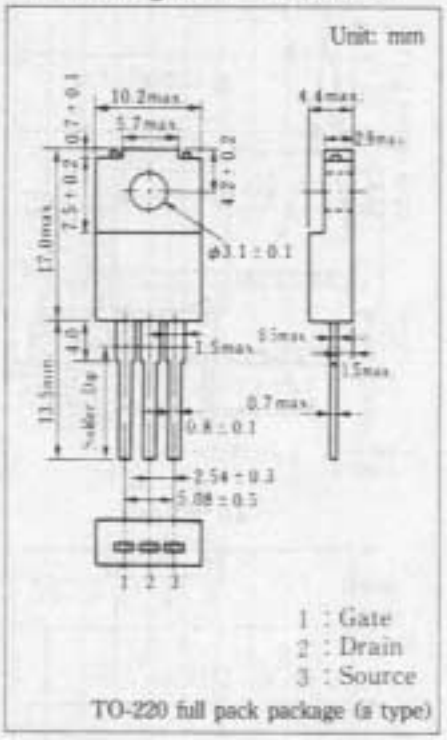
■ Features

- Low ON resistance R_{DS} (on) : R_{DS} (on) 1 = 0.08Ω (typ.)
- High switching rate : t_f = 180ns (typ.)
- No secondary breakdown
- For low voltage driving (V_{GS} = 4V)

■ Application

- DC-DC converter
- No contact relay
- Solenoid drive
- Motor drive

■ Package Dimensions



1 : Gate
2 : Drain
3 : Source

TO-220 full pack package (a type)

■ Absolute Maximum Ratings (Tc=25°C)

Item		Symbol	Value	Unit
Drain-source voltage		V_{DSS}	150	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	DC	I_D	20	A
	Peak-to-peak value	I_{DP}	40	
Power dissipation	Tc=25℃	P_D	45	W
	Ta=25℃		2.0	
Channel temperature		T_{ch}	150	℃
Storage temperature		T_{stg}	−55 − +150	℃

■ Electrical Characteristics (Tc=25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit
Drain current	I_{DSS}	V_{DS}=130V, V_{GS}=0			10	μA
Gate-source current	I_{GSS}	V_{GS}=±20V, V_{DS}=0			±1	μA
Drain-source voltage	V_{DSS}	I_D=1 mA, V_{GS}=0	150			V
Gate threshold voltage	V_{th}	V_{DS}=10V, I_D=1mA	1		2.5	V
Drain-source ON resistance	R_{DS}(on)1	V_{GS}=10V, I_D=10A		0.08	0.12	Ω
Drain-source ON resistance	R_{DS}(on)2	V_{GS}=4V, I_D=10A		0.09	0.135	Ω
Forward transfer admittance	|Yfs|	V_{DS}=10V, I_D=10A	10	20		S
Input capacitance	C_{iss}	V_{DS}=10V, V_{GS}=0, f=1MHz		3450		pF
Output capacitance	C_{oss}			600		pF
Reverse transfer capacitance	C_{rss}			150		pF
Turn-on time	t_{on}	V_{GS}=10V, I_D=10A, V_{DD}≒100V, R_L=10Ω		90		ns
Fall time	t_f			180		ns
Delay time	t_d(off)			770		ns